

20V, 2 A PNP/PNP low VCEsat (BISS) double transistor

14 December 2015

Product data sheet

1. General description

PNP/PNP low V_{CEsat} Breakthrough In Small Signal (BISS) double transistor in a leadless medium power DFN2020D-6 (SOT1118D) Surface-Mounted Device (SMD) plastic package with visible and solderable side pads.

NPN/NPN complement: PBSS4220PANS

2. Features and benefits

- Very low collector-emitter saturation voltage V_{CEsat}
- High collector current capability ${\rm I}_{\rm C}$ and ${\rm I}_{\rm CM}$
- High collector current gain h_{FE} at high I_C
- Reduced Printed-Circuit Board (PCB) requirements
- Exposed heat sink for excellent thermal and electrical conductivity
- High energy efficiency due to less heat generation
- Suitable for Automatic Optical Inspection (AOI) of solder joints
- AEC-Q101 qualified

3. Applications

- Load switch
- Battery-driven devices
- Power management
- Charging circuits
- LED lighting
- Power switches (e.g. motors, fans)

4. Quick reference data

Table I. Quick reference uata	Table 1.	Quick referenc	e data
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Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transistor							
V _{CEO}	collector-emitter voltage	open base		-	-	-20	V
I _C	collector current			-	-	-2	А
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms		-	-	-3	А

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Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transistor							
V _{CEsat}	collector-emitter saturation voltage	$\begin{split} &I_{C} = -0.7 \text{ A}; I_{B} = -7 \text{ mA}; \text{pulsed}; \\ &t_{p} \leq 300 \mu\text{s}; \delta \leq 0.02 ; \text{T}_{amb} = 25 ^{\circ}\text{C} \end{split}$		-	-145	-200	mV

5. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	E1	emitter TR1	6 5 4	C1 B2 E2
2	B1	base TR1		
3	C2	collector TR2	7 8	
4	E2	emitter TR2		
5	B2	base TR2	Transparent top view sym138	
6	C1	collector TR1		Transparent top view S DFN2020D-6 (SOT1118D)
7	C1	collector TR1	DI 112020D-0 (SOTTI10D)	
8	C2	collector TR2		

6. Ordering information

Table 3. Ordering information						
Type number	Package					
	Name	Description	Version			
PBSS5220PAPS	DFN2020D-6	DFN2020D-6: plastic, thermally enhanced ultra thin and small outline package; no leads; 6 terminals; body 2 x 2 x 0.65 mm	SOT1118D			

7. Marking

Table 4. Marking codes			
Type number	Marking code		
PBSS5220PAPS	3P		

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
Per transis	tor					
V _{CBO}	collector-base voltage	open emitter		-	-20	V
V _{CEO}	collector-emitter voltage	open base		-	-20	V
V _{EBO}	emitter-base voltage	open collector		-	-7	V
I _C	collector current			-	-2	А
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms		-	-3	А
I _B	base current			-	-0.3	А
I _{BM}	peak base current	single pulse; t _p ≤ 1 ms		-	-1	Α
P _{tot} total power diss	total power dissipation	ipation $T_{amb} \le 25 \ ^{\circ}C$	[1]	-	370	mW
			[2]	-	570	mW
			[3]	-	530	mW
			[4]	-	700	mW
Per device						_
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	510	mW
			[2]	-	780	mW
			[3]	-	730	mW
			[4]	-	960	mW
Tj	junction temperature			-	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

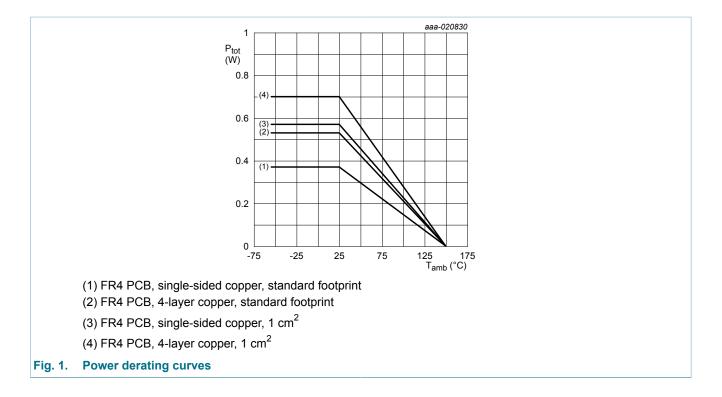
[2] Device mounted on an FR4 Printed-Circuit Board (PCB), single sided copper, tin-plated; mounting pad for collector 1 cm².

[3] Device mounted on an FR4 Printed-Circuit Board (PCB), 4-layer copper, tin-plated and standard footprint.

 [4] Device mounted on an FR4 Printed-Circuit Board (PCB), 4-layer copper, tin-plated; mounting pad for collector 1 cm².

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9. Thermal characteristics

collector 1 cm².

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transist	or		!				
R _{th(j-a)} thermal resistance from junction to ambient		in free air	[1]	-	-	338	K/W
		[2]	-	-	219	K/W	
	ampient		[3]	-	-	236	K/W
			[4]	-	-	179	K/W
Per device							
R _{th(j-a)}	thermal resistance	in free air	[1]	-	-	246	K/W
	from junction to ambient		[2]	-	-	161	K/W
	ampient		[3]	-	-	172	K/W
			[4]	-	-	131	K/W

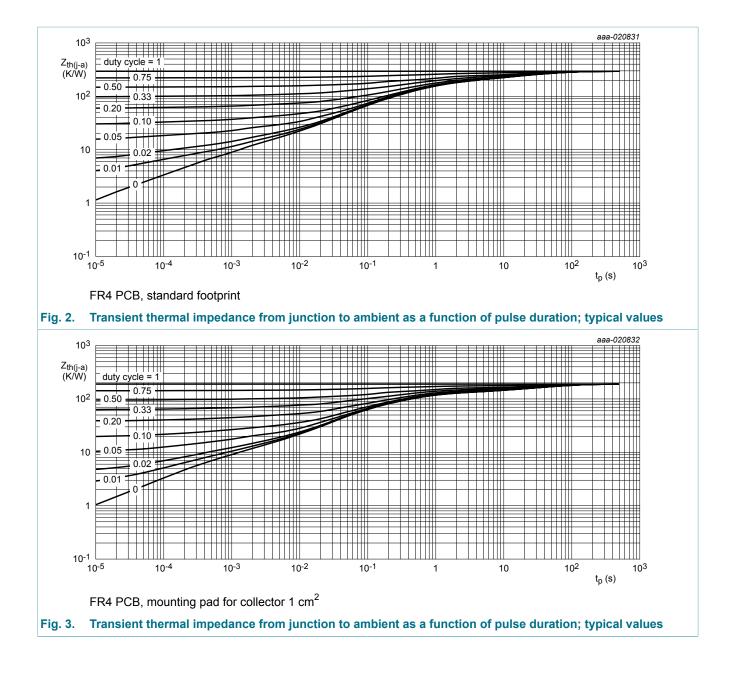
[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for collector 1 cm².

[3] Device mounted on an FR4 Printed-Circuit Board (PCB), 4-layer copper, tin-plated and standard footprint.
 [4] Device mounted on an FR4 Printed-Circuit Board (PCB), 4-layer copper, tin-plated, mounting pad for

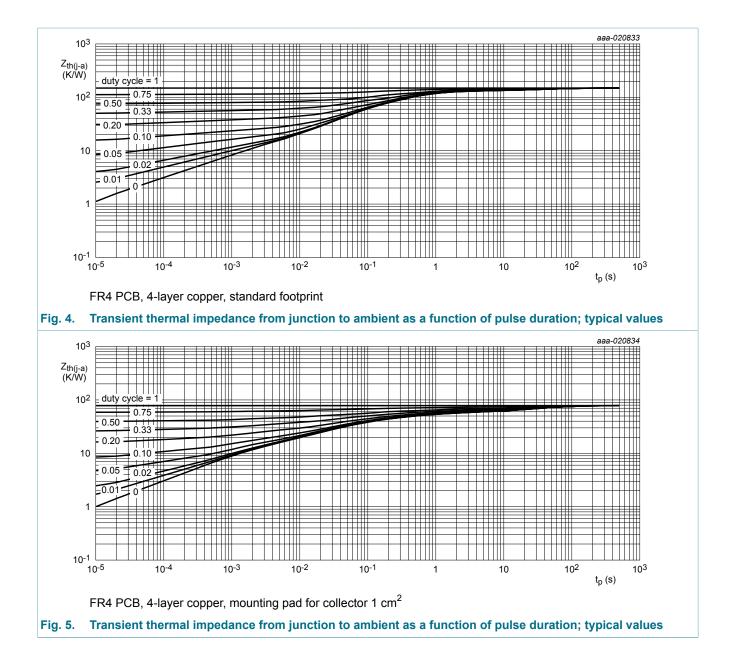
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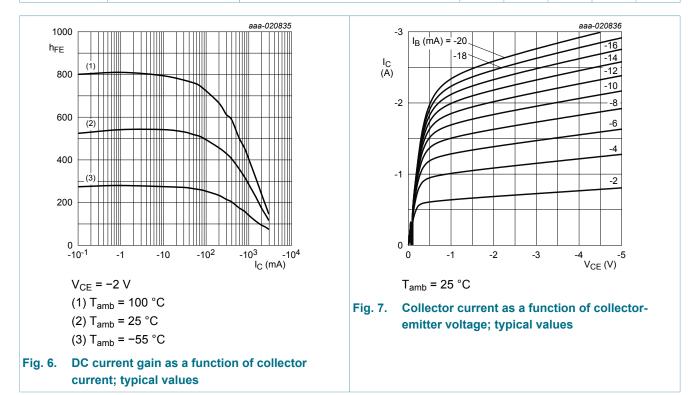
10. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per transis	stor					
I _{CBO} collector-base cut-off		V_{CB} = -16 V; I _E = 0 A; T _{amb} = 25 °C	-	-	-100	nA
	current	V_{CB} = -16 V; I _E = 0 A; T _j = 150 °C	-	-	-50	μA
I _{CES}	collector-emitter cut-off current	V_{CE} = -16 V; V_{BE} = 0 V; T_{amb} = 25 °C	-	-	-100	nA
I _{EBO}	emitter-base cut-off current	V_{EB} = -5 V; I _C = 0 A; T _{amb} = 25 °C	-	-	-100	nA
h _{FE}	DC current gain	$\begin{split} V_{CE} &= -2 \text{ V; } I_C = -100 \text{ mA; pulsed;} \\ t_p &\leq 300 \mu\text{s; } \delta \leq 0.02 ; T_{amb} = 25 ^\circ\text{C} \end{split}$	250	400	-	
		V_{CE} = -2 V; I _C = -500 mA; pulsed; t _p ≤ 300 µs; δ ≤ 0.02 ; T _{amb} = 25 °C	210	300	-	
		$V_{CE} = -2 \text{ V; } I_C = -1 \text{ A; pulsed;}$ $t_p \le 300 \mu\text{s; } \delta \le 0.02 \text{ ; } T_{amb} = 25 ^\circ\text{C}$	160	250	-	
		V_{CE} = -2 V; I _C = -2 A; pulsed; t _p ≤ 300 µs; δ ≤ 0.02	100	150	-	
V _{CEsat}	collector-emitter saturation voltage	I_{C} = -0.5 A; I_{B} = -50 mA; pulsed; $t_{p} \le 300 \ \mu$ s; δ ≤ 0.02 ; T_{amb} = 25 °C	-	-70	-110	mV
		I_{C} = -1 A; I_{B} = -50 mA; pulsed; $t_{p} \le 300 \ \mu$ s; δ ≤ 0.02 ; T_{amb} = 25 °C	-	-150	-220	mV
		I_{C} = -0.7 A; I_{B} = -7 mA; pulsed; $t_{p} \le 300 \ \mu$ s; δ ≤ 0.02 ; T_{amb} = 25 °C	-	-145	-200	mV
		I_{C} = -2 A; I_{B} = -200 mA; pulsed; $t_{p} \le 300$ μs; δ ≤ 0.02	-	-260	-390	mV
R _{CEsat}	collector-emitter saturation resistance	I_{C} = -1 A; I_{B} = -50 mA; pulsed; $t_{p} \le 300 \ \mu$ s; δ ≤ 0.02 ; T_{amb} = 25 °C	-	-	220	mΩ
V _{BEsat}	base-emitter saturation voltage	I_{C} = -0.5 A; I_{B} = -50 mA; pulsed; $t_{p} \le 300 \ \mu$ s; δ ≤ 0.02 ; T_{amb} = 25 °C	-	-0.9	-1	V
		I_{C} = -1 A; I_{B} = -50 mA; pulsed; $t_{p} \le 300 \ \mu$ s; δ ≤ 0.02; T_{amb} = 25 °C	-	-0.94	-1.1	V
		I _C = -2 A; I _B = -200 mA; pulsed; t _p ≤ 300 μs; δ ≤ 0.02; T _{amb} = 25 °C	-	-1.13	-1.25	V
V _{BE}	base-emitter voltage	I_{C} = -0.5 A; V_{CE} = -2 V; T_{amb} = 25 °C	-	-0.75	-0.9	V
t _d	delay time	I _C = -1 A; I _{Bon} = -50 mA; I _{Boff} = 50 mA;	-	10	-	ns
t _r	rise time	T _{amb} = 25 °C	-	50	-	ns
t _{on}	turn-on time		_	60	-	ns

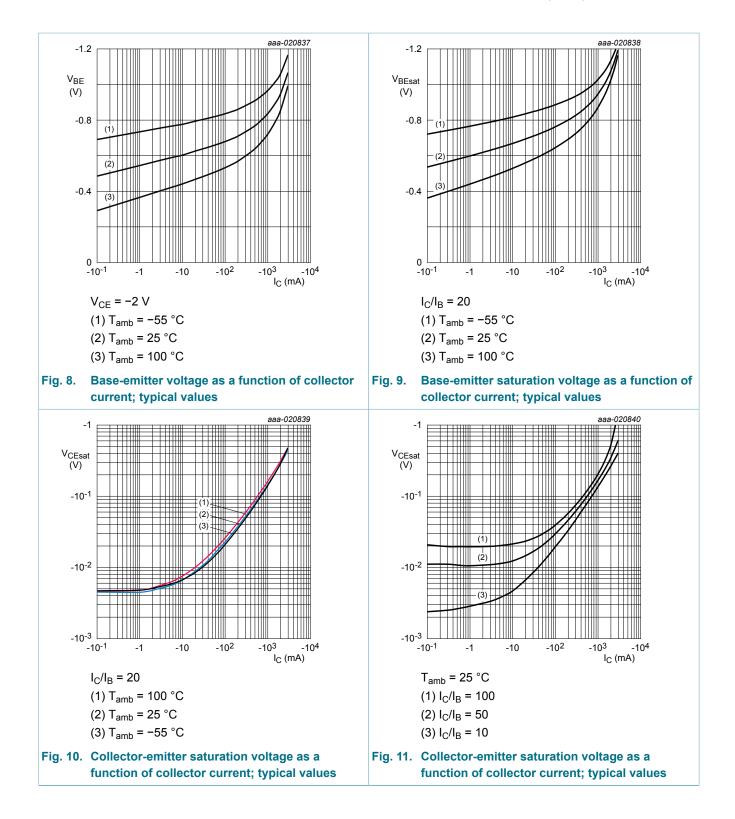
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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
t _s	storage time		-	200	-	ns
t _f	fall time	_	-	45	-	ns
t _{off}	turn-off time	-	-	245	-	ns
f _T	transition frequency	V_{CE} = -10 V; I _C = -50 mA; f = 100 MHz; T _{amb} = 25 °C	-	95	-	MHz
C _c	collector capacitance	V _{CB} = -10 V; I _E = 0 A; i _e = 0 A; f = 1 MHz; T _{amb} = 25 °C	-	25	-	pF



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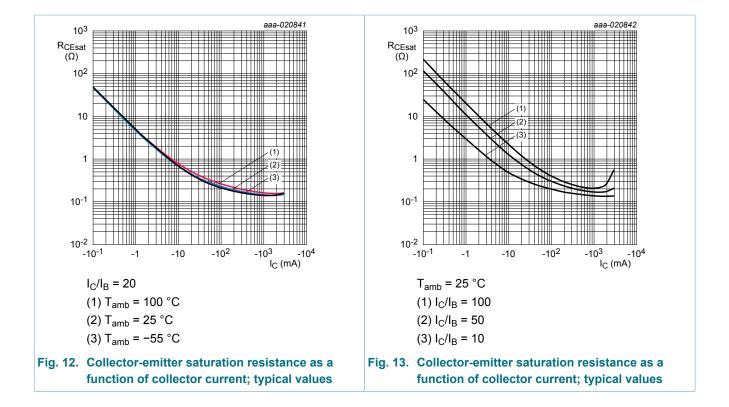
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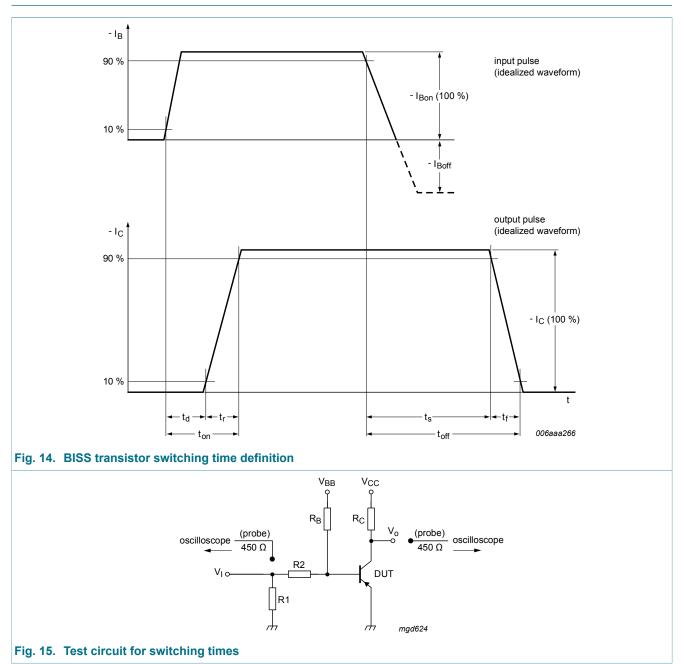
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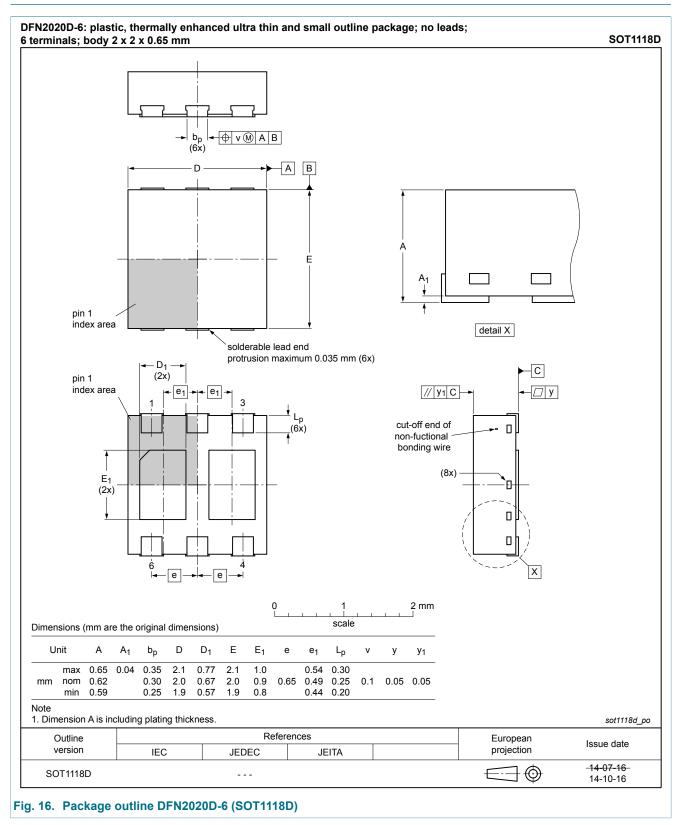
11. Test information

11.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101* - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

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12. Package outline

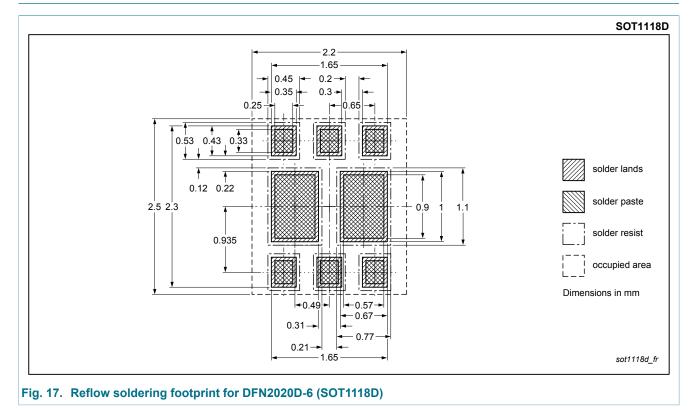


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13. Soldering



14. Revision history

Table 8. Revision history						
Data sheet ID	Release date	Data sheet status	Change notice	Supersedes		
PBSS5220PAPS v.2	20151214	Product data sheet	-	PBSS5220PAPS v.1		
Modifications:	Product status changed					
PBSS5220PAPS v.1	20150925	Objective data sheet	-	-		

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15. Legal information

15.1 Data sheet status

Document status [1][2]	Product status [<u>3]</u>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

 Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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